MMBFJ309L, MMBFJ310L, SMMBFJ310L

JFET - VHF/UHF Amplifier Transistor

N-Channel

Features

- Drain and Source are Interchangeable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and **PPAP** Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	25	Vdc
Gate-Source Voltage	V _{GS}	25	Vdc
Gate Current	I _G	10	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	PD	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Junction and Storage Temperature	T _J , T _{stg}	–55 to +150	°C

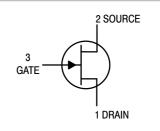
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. $FR-5 = 1.0 \times 0.75 \times 0.062$ in.



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SOT-23 (TO-236) **CASE 318** STYLE 10

MARKING DIAGRAM



- 6x = Device Code
 - x = U for MMBFJ309L
 - x = T for MMBFJ310L, SMMBFJ310L
- = Date Code* Μ
- = Pb-Free Package

(Note: Microdot may be in either location) *Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]				
MMBFJ309LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel				
MMBFJ310LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel				
SMMBFJ310LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel				
SMMBFJ310LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel				

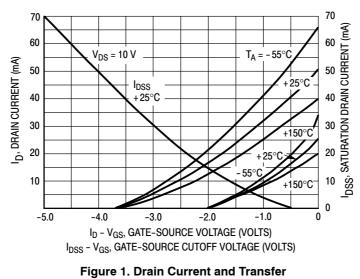
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBFJ309L, MMBFJ310L, SMMBFJ310L

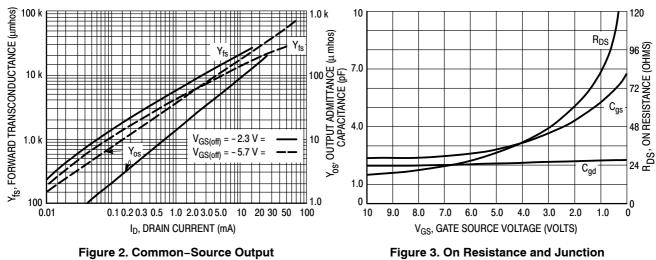
ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Тур	Мах	Unit	
OFF CHARACTERISTICS							
Gate–Source Breakdown Voltage $(I_G = -1.0 \ \mu Adc, V_{DS} = 0)$			-25	-	-	Vdc	
Gate Reverse Current (V _{GS} = -15 Vdc) (V _{GS} = -15 Vdc, T _A = 125°C)					- 1.0 - 1.0	nAdc μAdc	
Gate Source Cutoff Voltage (V _{DS} = 10 Vdc, I _D = 1.0 nAdc)	MMBFJ309 MMBFJ310, SMMBFJ310	V _{GS(off)}	-1.0 -2.0	-	-4.0 -6.5	Vdc	
ON CHARACTERISTICS							
Zero-Gate-Voltage Drain Current $(V_{DS} = 10 \text{ Vdc}, V_{GS} = 0)$	MMBFJ309 MMBFJ310, SMMBFJ310	I _{DSS}	12 24		30 60	mAdc	
Gate-Source Forward Voltage (I _G = 1.0 mAdc, V _{DS} = 0)		V _{GS(f)}	-	-	1.0	Vdc	
SMALL-SIGNAL CHARACTERISTICS							
Forward Transfer Admittance $(V_{DS} = 10 \text{ Vdc}, I_D = 10 \text{ mAdc}, f = 1.0 \text{ kHz})$		Y _{fs}	8.0	-	18	mmhos	
Output Admittance (V _{DS} = 10 Vdc, I _D = 10 mAdc, f = 1.0 kHz)		y _{os}	-	_	250	μmhos	
Input Capacitance (V _{GS} = -10 Vdc, V _{DS} = 0 Vdc, f = 1.0 MHz)		C _{iss}	-	-	5.0	pF	
Reverse Transfer Capacitance (V _{GS} = -10 Vdc, V _{DS} = 0 Vdc, f = 1.0 MHz)		C _{rss}	-	-	2.5	pF	
Equivalent Short-Circuit Input Noise Voltage $(V_{DS} = 10 \text{ Vdc}, I_D = 10 \text{ mAdc}, f = 100 \text{ Hz})$		ēn	-	10	-	nV/\sqrt{Hz}	

MMBFJ309L, MMBFJ310L, SMMBFJ310L



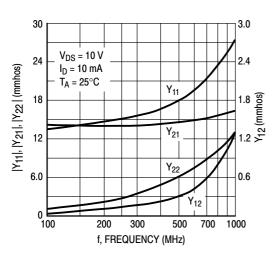
Characteristics versus Gate-Source Voltage

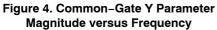


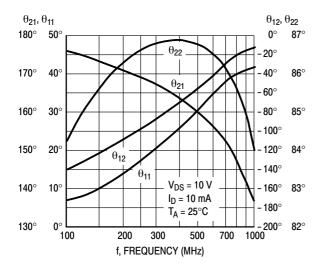
Admittance and Forward Transconductance versus Drain Current

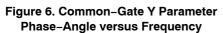
Capacitance versus Gate-Source Voltage

MMBFJ309L, MMBFJ310L, SMMBFJ310L









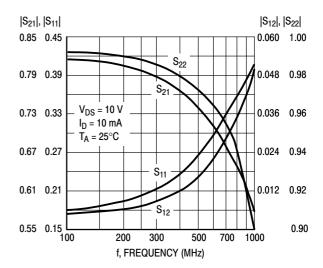
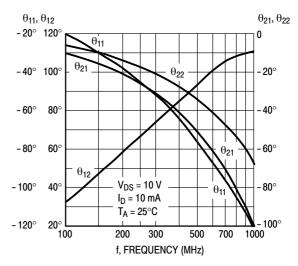


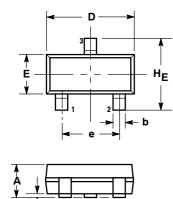
Figure 5. Common–Gate S Parameter Magnitude versus Frequency

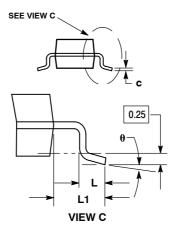




PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 ISSUE AP





	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
Е	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
ΗE	2.10	2.40	2.64	0.083	0.094	0.104	
θ	0°		10°	0°		10°	

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH

CONTROLLING DIMENSION: INCH.

PROTRUSIONS OR GATE BURRS

2. SOURCE 3. GATE

STYLE 10

PIN 1. DRAIN

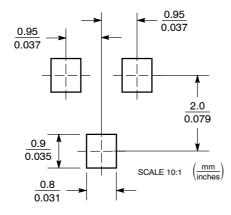
NOTES

2

3

4.

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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